(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
6 March 2008 (06.03.2008)

PCT

(10) International Publication Number
WO 2008/027473 A3

(51) International Patent Classification:
H01L 21/768 (2006.01) *H01L 21/336* (2006.01)
H01L 21/285 (2006.01)

(21) International Application Number:
PCT/US2007/019073

(22) International Filing Date: 29 August 2007 (29.08.2007)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10 2006 040 764.4 31 August 2006 (31.08.2006) DE
11/697,890 9 April 2007 (09.04.2007) US

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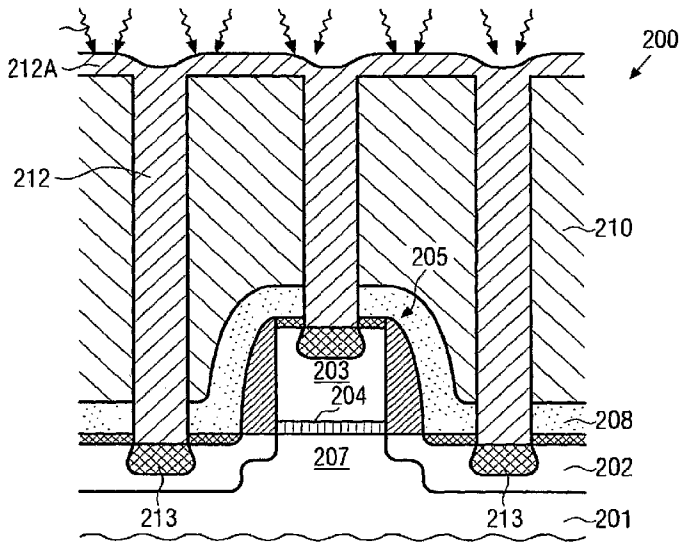
(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

[Continued on next page]

(54) **Title:** A TRANSISTOR HAVING A LOCALLY PROVIDED METAL SILICIDE REGION IN CONTACT AREAS AND A METHOD OF FORMING THE TRANSISTOR



(57) **Abstract:** By performing a silicidation process on the basis of a patterned dielectric layer, such as an interlayer dielectric material, the respective metal silicide portions may be provided in a highly localized manner at the respective contact regions, while the overall amount of metal silicide may be significantly reduced. In this way, a negative influence of the stress of metal silicide on the channel regions of field effect transistors may be significantly reduced, while nevertheless maintaining a low contact resistance.

WO 2008/027473 A3

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(88) Date of publication of the international search report:
17 April 2008